

NPN SILICON POWER TRANSISTORS

... designed for use in general purpose power amplifier application

FEATURES:

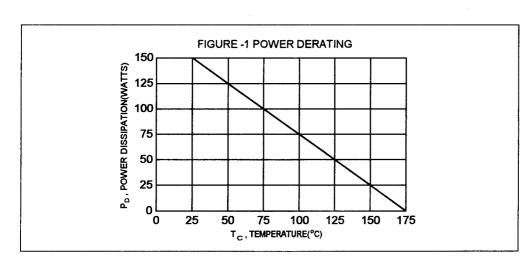
- * Very Low Saturation Voltage and High Gain for reduced load Operation.
- * Faster Switchingent Times
- * Lower Switching Losses
- * Lower On State Voltage Drop

MAXIMUM RATINGS

Characteristic	Symbol	BUW50	Unit
Collector-Emitter Voltage	V _{CEO}	125	V
Collector-Emitter Voltage V _{BE} =-1.5V	V _{CEV}	250	v
Emitter-Base Voltage	V _{EBO}	7.0	V
Collector Current - Continuous - Peak	I _C	25 50	A
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	150 1.0	W/°C
Operating and Storage Junction Temperature Range	T _J ,T _{STG}	-65 to +175	°C

THERMAL CHARACTERISTICS

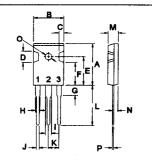
Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	Rθjc	1.0	°C/W



NPN BUW50

25 AMPERE POWER TRANASISTORS 125 VOLTS 150 WATTS





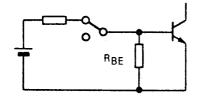
PIN 1.BASE 2.COLLECTOR 3.EMITTER

DIM	MILLIMETERS			
5,,,,,	MIN	MAX		
Α	20.63	22.38		
В	15.38	16.20		
С	1.90	2.70		
D	5.10	6.10		
Е	14.81	15.22		
F	11.72	12.84		
G	4.20	4.50		
н	1.82	2.46		
1	2.92	3.23		
J	0.89	1.53		
K	5.26	5.66		
L	18.50	21.50		
М	4.68	5.36		
N	2.40	2.80		
0	3.25	3.65		
Р	0.55	0.70		

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

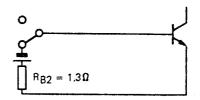
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (1) (I _C = 0.2 A, I _B = 0,L= 25 mH)	V _{CEO(sus)}	125		V
Emitter-Base Voltage (I _E = 20mA, I _C = 0)	V _{EBO}	7.0		V
Collector Cutoff Current (V _{CE} = 250 V, V _{BE} = -1.5 V)	I _{CEV}		100	uA
Emitter Cutoff Current (V _{EB} = 5.0 V, I _C = 0)	EBO		1.0	mA
ON CHARACTERISTICS (1)				
Collector-Emitter Saturation Voltage (I _C = 10 A, I _B = 0.5 A) (I _C = 20 A, I _B = 2.0 A)	V _{CE(sat)}		0.9 1.0	V
Base-Emitter Saturation Voltage (I _C = 20 A, I _B = 2.0 A)	V _{BE(sat)}		1.6	٧
SWITCHING CHARATERISTICS			·	*,,,,,,
Turn-on Time $V_{CC} = 60V, I_C = 10A$	t on		1.9	us
Storage Time I _{B1} = 1.0A PW= 20 us	ts		1.5	us
Fall Time	t,		0.5	us

⁽¹⁾ Pulse Test: Pulse Width =300 us, Duty Cycle ≦ 2.0%



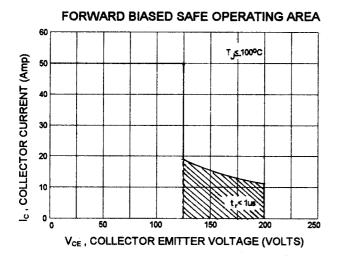
TRANSISTOR FORWARD BIASED

- -During the turn-on
- -During the turn-off without negative base-emitter voltage and $4.7\,\Omega {\le R_{BE}} \le 50.\Omega$

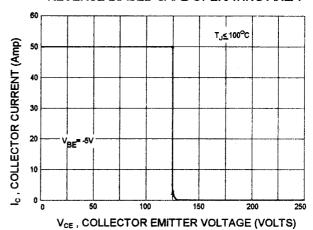


TRANSISTOR FORWARD BIASED

-During the turn-off without negative base-emitter voltage



REVERSE BIASED SAFE OPERATING AREA





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